

TSM7P06CP

60V P-Channel Power MOSFET

TO-252



Pin Definition:

1. Gate
2. Drain
3. Source

Key Parameter Performance

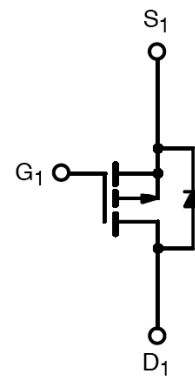
Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	180
	$V_{GS} = -4.5V$	220
Q_g	8.2	nC

Ordering Information

Part No.	Package	Packing
TSM7P06CP ROG	TO-252	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



P-Channel MOSFET

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	-7
		$T_C = 100^\circ\text{C}$	-4.4
Pulsed Drain Current ^(Note 1)	I_{DM}	-28	A
Single Pulse Avalanche Energy ^(Note 2)	E_{AS}	32	mJ
Single Pulse Avalanche Current ^(Note 1)	I_{AS}	-8	A
Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	15.6	W
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-50 to +150	$^\circ\text{C}$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	8	$^\circ\text{C/W}$
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	62	

Electrical Specifications ($T_C=25^\circ\text{C}$ unless otherwise noted)

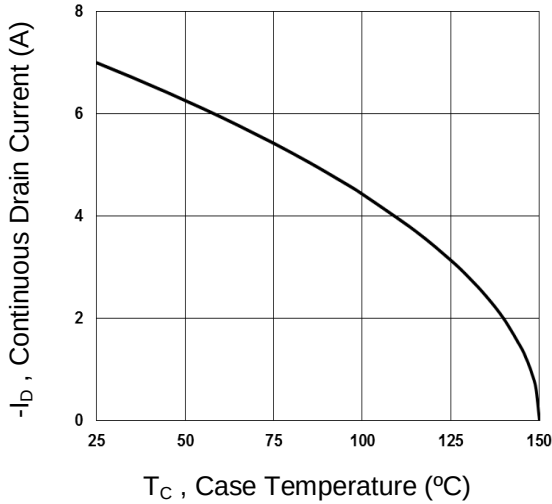
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV_{DSS}	-60	--	--	V
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -3A$	$R_{DS(ON)}$	--	153	180	mΩ
	$V_{GS} = -4.5V, I_D = -1.5A$		--	198	220	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	$V_{GS(TH)}$	-1.2	-1.6	-2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = -60V, V_{GS} = 0V$	I_{DSS}	--	--	-1	μA
	$V_{DS} = -48V, V_{GS} = 0V, T_C = 125^{\circ}C$		--	--	-10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	±100	nA
Forward Transconductance ^(Note 3)	$V_{DS} = -10V, I_D = -2A$	g_{fs}	--	3	--	S
Dynamic						
Total Gate Charge ^(Note 3,4)	$V_{DS} = -30V, I_D = -3A, V_{GS} = -10V$	Q_g	--	8.2	--	nC
Gate-Source Charge ^(Note 3,4)		Q_{gs}	--	1.8	--	
Gate-Drain Charge ^(Note 3,4)		Q_{gd}	--	1.5	--	
Input Capacitance	$V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz$	C_{iss}	--	425	--	pF
Output Capacitance		C_{oss}	--	35	--	
Reverse Transfer Capacitance		C_{rss}	--	20	--	
Switching						
Turn-On Delay Time ^(Note 3,4)	$V_{DD} = -30V, I_D = -1A, R_{GEN} = 6\Omega$	$t_{d(on)}$	--	5.2	--	ns
Turn-On Rise Time ^(Note 3,4)		t_r	--	19	--	
Turn-Off Delay Time ^(Note 3,4)		$t_{d(off)}$	--	35	--	
Turn-Off Fall Time ^(Note 3,4)		t_f	--	10.6	--	
Source-Drain Diode Ratings and Characteristic						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I_S	--	--	-7	A
Maximum Pulse Drain-Source Diode Forward Current		I_{SM}	--	--	-28	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_S = -1A$	V_{SD}	--	--	-1	V

Note:

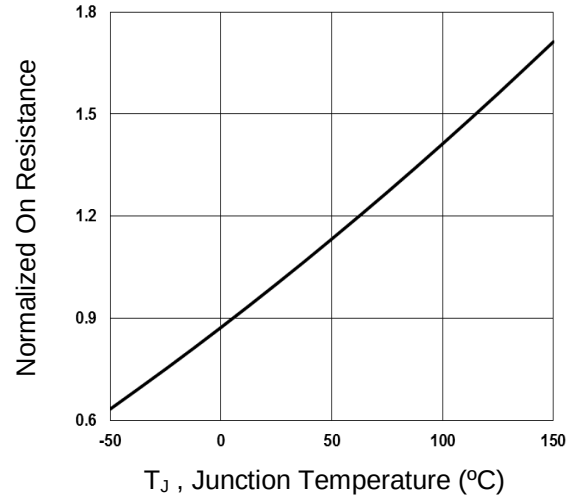
- Pulse width limited by safe operating area
- $L=1\text{mH}, I_{AS}=-8A, V_{DD}=-25V, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
- Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- Switching time is essentially independent of operating temperature.

Electrical Characteristics Curve

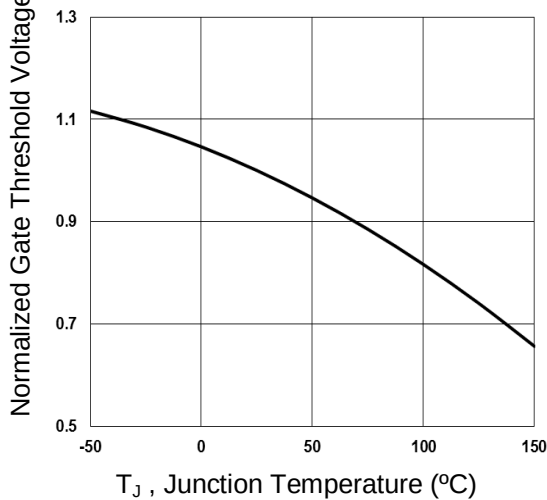
Continuous Drain Current vs. T_C



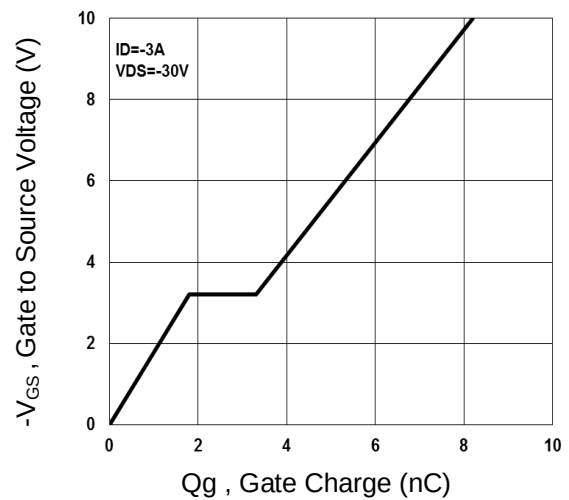
Normalized $R_{DS(on)}$ vs. T_J



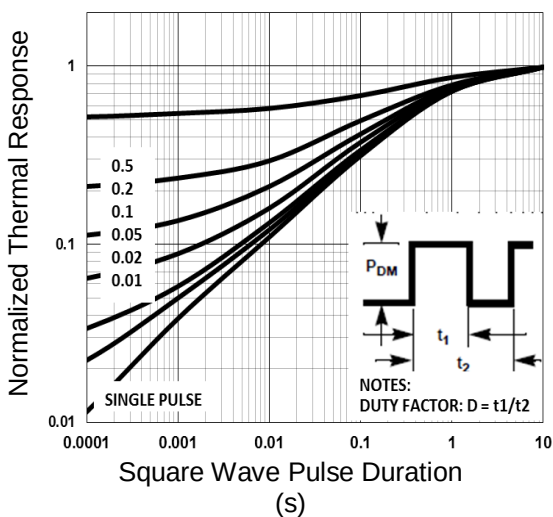
Normalized V_{th} vs. T_J



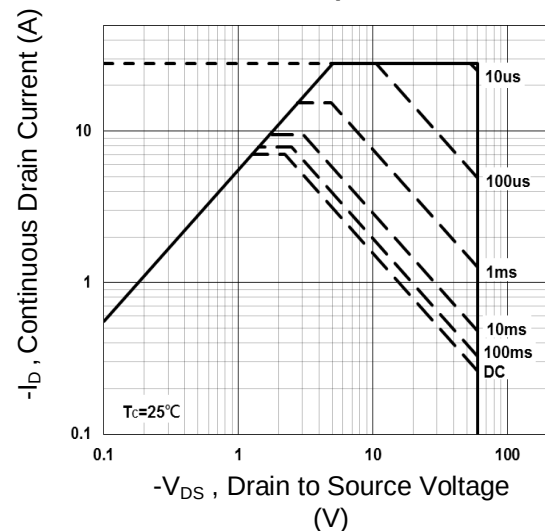
Gate Charge Waveform



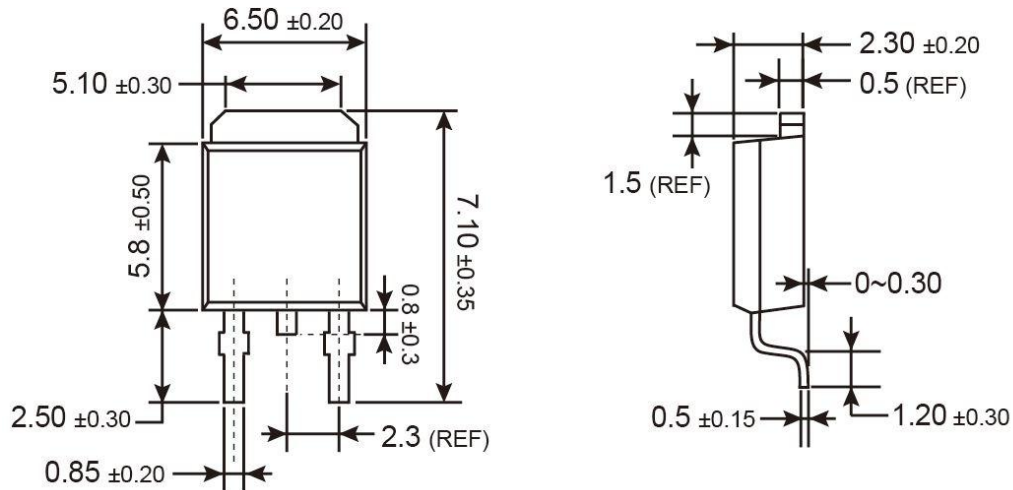
Normalized Transient Impedance



Maximum Safe Operation Area

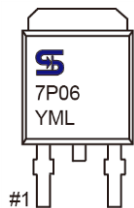


TO-252 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

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